L Number	Hits	Search Text	DB	Time stamp
-	1182	(passiv\$8 near (layer or region or film or medium))	USPAT;	2003/07/14 09:22
		and semiconductor and monolithic and integrated	US-PGPUB;	
		and substrate	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	((passiv\$8 near (layer or region or film or medium))	USPAT;	2002/11/22 08:59
		and semiconductor and monolithic and integrated	US-PGPUB;	
		and substrate) and VCSEI and ((active near (layer or	EPO; JPO;	
		device or film or region or medium)) with amplif\$5)	DERWENT;	,
		and (photodiode or (photo near diode)) and	IBM_TDB	
,		(photodetect\$5 or (photo near detect\$5))		
-	3	((passiv\$8 near (layer or region or film or medium))	USPAT;	2002/11/22 09:02
		and semiconductor and monolithic and integrated	US-PGPUB;	
		and substrate) and VCSEI and ((active near (layer or	EPO; JPO;	
		device or film or region or medium)) AND amplif\$5)	DERWENT;	
		and (photodiode or (photo near diode)) and	IBM_TDB	
		(photodetect\$5 or (photo near detect\$5))		
<u>-</u>	6	(passiv\$8 near (layer or region or film or medium))	USPAT;	2002/11/22 09:13
		and semiconductor and integrated and substrate and	US-PGPUB;	
		VCSEI and ((active near (layer or device or film or	EPO; JPO;	
		region or medium)) AND amplif\$5) and (photodiode	DERWENT;	
		or (photo near diode)) and (photodetect\$5 or (photo	IBM_TDB	
		near detect\$5))		
-	1	(passiv\$8 near (layer or region or film or medium))	USPAT;	2002/11/22 09:04
		and semiconductor and 372/50 and substrate and	US-PGPUB;	
		VCSEI and ((active near (layer or device or film or	EPO; JPO;	
		region or medium)) AND amplif\$5) and (photodiode	DERWENT;	
		or (photo near diode)) and (photodetect\$5 or (photo	IBM_TDB	
		near detect\$5))		
-	1	(passiv\$8 near (layer or region or film or medium))	USPAT;	2002/11/22 09:11
		and semiconductor and 372/\$ and substrate and	US-PGPUB;	
		VCSEI and ((active near (layer or device or film or	EPO; JPO;	
		region or medium)) AND amplif\$5) and (photodiode	DERWENT;	
	:	or (photo near diode)) and (photodetect\$5 or (photo	IBM_TDB	
	_	near detect\$5))		
-	9	((passiv\$8 or insulat\$5) near (layer or region or film	USPAT;	2002/11/22 09:13
		or medium)) and semiconductor and 372/\$ and	US-PGPUB;	
		substrate and VCSEI and ((active near (layer or	EPO; JPO;	
		device or film or region or medium)) AND amplif\$5)	DERWENT;	
		and (photodiode or (photo near diode)) and	IBM_TDB	
		(photodetect\$5 or (photo near detect\$5))		
-	17	((passiv\$8 or insulat\$5) near (layer or region or film	USPAT;	2002/11/22 09:41
		or medium)) and semiconductor and integrated and	US-PGPUB;	
		substrate and VCSEI and ((active near (layer or	EPO; JPO;	
		device or film or region or medium)) AND amplif\$5)	DERWENT;	
		and (photodiode or (photo near diode)) and	IBM_TDB	
		(photodetect\$5 or (photo near detect\$5))	LICDAT	0000/11/00 00 11
-	17	((passiv\$8 or insulat\$5) near (layer or region or film	USPAT;	2002/11/22 09:41
		or medium)) and semiconductor and substrate and	US-PGPUB;	
į		VCSEI and ((active near (layer or device or film or	EPO; JPO;	
ļ		region or medium)) AND amplif\$5) and (photodiode	DERWENT;	
		or (photo near diode)) and (photodetect\$5 or (photo	IBM_TDB	
		near detect\$5))	i	<u> </u>

-	14	(((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:42
-	17	(diode near laser) (((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:17
-	11	(photodetect\$5 or (photo near detect\$5))) and diode ((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:22
-	6	((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) not (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27
-	2	mesa and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27
-	11	amplif\$5 and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27

-	11	(((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near detect\$5))) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))) not (amplif\$5 and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and (photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium)))) (((((passiv\$8 or insulat\$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium))) AND t (amplif\$5 and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium))) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or medium))) AND t (amplif\$5 and (((((passiv\$8 or insulat\$5) near (layer or region or film or medium))) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif\$5) and (photodiode or (photo near diode)) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:28
-	24698	(photodetect\$5 or (photo near detect\$5))) and diode) and (contact near (layer or device or region or film or medium)))) (substrate near3 (GaAs or AsGa))	USPAT; US-PGPUB;	2003/07/25 12:01
-	1390	(substrate near3 (GaN or NGa))	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/22 11:28
-	17941	(substrate near3 (InP or PIn))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/22 11:28
-	78	((substrate near3 (GaAs or AsGa))) and ((substrate near3 (GaN or NGa))) and ((substrate near3 (InP or PIn)))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/22 11:29
-	0	"11" and photodiode	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/22 11:29
			DERWENT; IBM_TDB	

-	0	("11" and photodiode) and (photodiode or	USPAT;	2002/11/22 11:30
		photodetect\$5)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	11	(((substrate near3 (GaAs or AsGa))) and ((substrate	USPAT;	2002/11/22 11:30
		near3 (GaN or NGa))) and ((substrate near3 (InP or	US-PGPUB;	
		PIn)))) and VCSEI	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	543	((passiv\$8 near (layer or region or film or medium))	USPAT;	2003/07/14 13:41
		with (window or aperture)) and (semiconductor or	US-PGPUB;	
		VCSEL) and substrate and active	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6	((passiv\$8 near (layer or region or film or medium))	USPAT;	2003/07/14 13:43
		with (window or aperture)) and (VCSEL) and	EPO; JPO;	
		substrate and active	DERWENT;	
			IBM TDB	